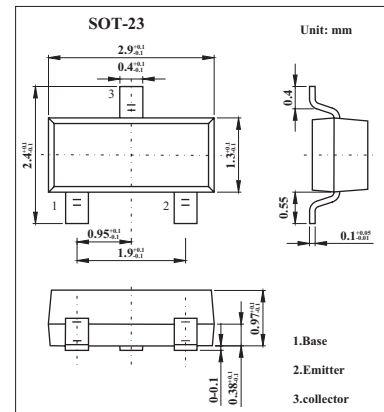


PNP Switching Transistors

BSR15

■ Features

- High current (max. 600 mA).
- Low voltage (max. 60 V).

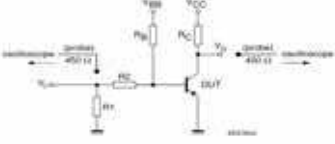
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-60	V
Collector-emitter voltage	V_{CE0}	-40	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-600	mA
Peak collector current	I_{CM}	-800	mA
Peak base current	I_{BM}	-200	mA
Total power dissipation	P_{tot}	250	mW
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th\ j-a}$	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BSR15

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector cutoff current	ICBO	$I_E = 0; V_{CB} = -50\text{ V}$			-20	nA	
		$I_E = 0; V_{CB} = -50\text{ V}; T_j = 150^\circ\text{C}$			-20	μA	
Emitter cutoff current	IEBO	$I_C = 0; V_{EB} = -5\text{ V}$			-50	nA	
DC current gain	hFE	$I_C = -0.1\text{ mA}; V_{CE} = -10\text{ V}$	35				
		$I_C = -1\text{ mA}; V_{CE} = -10\text{ V}$	50				
		$I_C = -10\text{ mA}; V_{CE} = -10\text{ V}$	75				
		$I_C = -150\text{ mA}; V_{CE} = -10\text{ V}^*$	100		300		
		$I_C = -500\text{ mA}; V_{CE} = -10\text{ V}; ^*$	30				
collector-emitter saturation voltage	VCEsat	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$			-400	mV	
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$			-1.6	V	
base-emitter saturation voltage	VBEsat	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$			-1.3	V	
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$			-2.6	V	
Collector capacitance	Cc	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$			8	pF	
Emitter capacitance	Ce	$I_C = i_c = 0; V_{EB} = -2\text{ V}; f = 1\text{ MHz}$			30		
Transition frequency	fr	$I_C = -50\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	200			MHz	
Turn-on time	ton	$I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA}; I_{Boff} = 15\text{ mA}$ (see Fig)			40	ns	
Delay time	td	 <p> $V_i = -9.5\text{ V}; T = 500\text{ }\mu\text{s}; t_p = 10\text{ }\mu\text{s}; t_r = t_f \leq 3\text{ ns};$ $R_1 = 68\text{ }\Omega; R_2 = 325\text{ }\Omega; R_B = 325\text{ }\Omega; R_C = 160\text{ }\Omega;$ $V_{BB} = 3.5\text{ V}; V_{CC} = -29.5\text{ V};$ Oscilloscope: input impedance $Z_i = 50\text{ }\Omega$. </p>			12	ns	
Rise time	tr					30	ns
Turn-off time	toff					365	ns
Storage time	ts					300	ns
Fall time	tf					65	ns

* Pulse test: $t_p \leq 300\text{ }\mu\text{s}; d \leq 0.02$.

■ Marking

Marking	T7
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